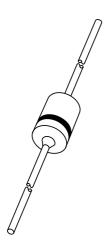
## DISCRETE SEMICONDUCTORS

## DATA SHEET



# **1N914** High-speed diode

Product specification Supersedes data of 1996 Sep 03 1999 May 26





### **High-speed diode**

1N914

#### **FEATURES**

#### Hermetically sealed leaded glass SOD27 (DO-35) package

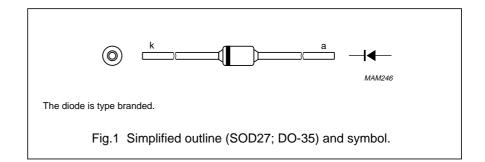
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 225 mA.

#### **APPLICATIONS**

• High-speed switching.

#### **DESCRIPTION**

The 1N914 is a high-speed switching diode fabricated in planar technology, and encapsulated in a hermetically sealed leaded glass SOD27 (DO-35) package.



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		_	100	V
$V_R$	continuous reverse voltage		_	75	V
I <sub>F</sub>	continuous forward current	see Fig.2; note 1	_	75	mA
I <sub>FRM</sub>	repetitive peak forward current		_	225	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	A
		t = 1 ms	_	1	A
		t = 1 s	_	0.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		_	175	°C

#### Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

## High-speed diode

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#### **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 mA; see Fig.3	1	V
I <sub>R</sub>	reverse current	see Fig.5		
		V <sub>R</sub> = 20 V	25	nA
		V <sub>R</sub> = 75 V	5	μΑ
		V <sub>R</sub> = 20 V; T <sub>j</sub> = 150 °C	50	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 \text{ MHz}$ ; $V_R = 0$ ; see Fig.6	4	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.7	8	ns
		when switched from $I_F$ = 10 mA to $I_R$ = 60 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.7	4	ns
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 50$ mA; $t_r = 20$ ns; see Fig.8	2.5	V

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

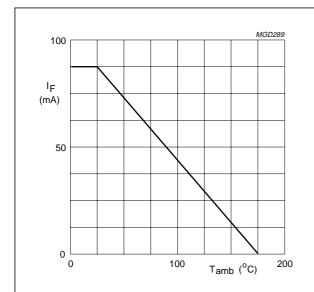
#### Note

1. Device mounted on a printed circuit-board without metallization pad.

## High-speed diode

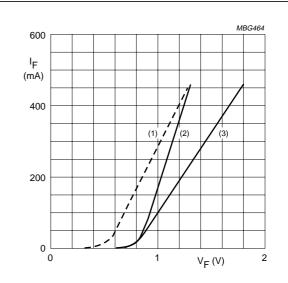
1N914

#### **GRAPHICAL DATA**



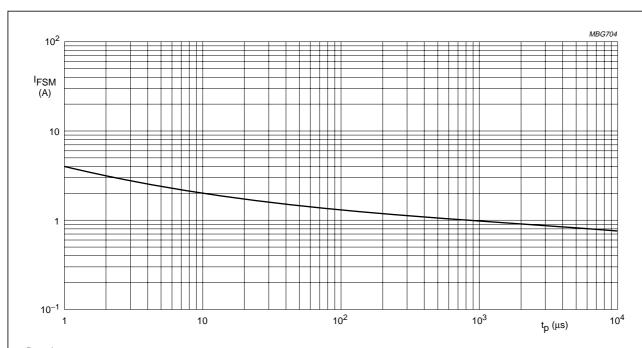
Device mounted on an FR4 printed-circuit board; lead length 10 mm.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1)  $T_j = 175$  °C; typical values.
- (2)  $T_i = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



Based on square wave currents.

 $T_j$  = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

1.2

1.0

0.8

0.6

0.4

C<sub>d</sub> (pF)

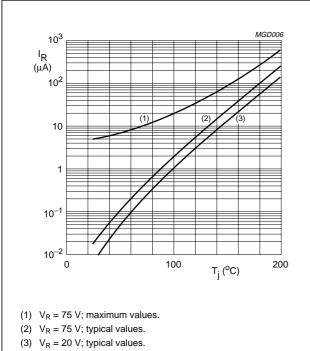
## High-speed diode

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MGD004

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 $V_{R}(V)$ 



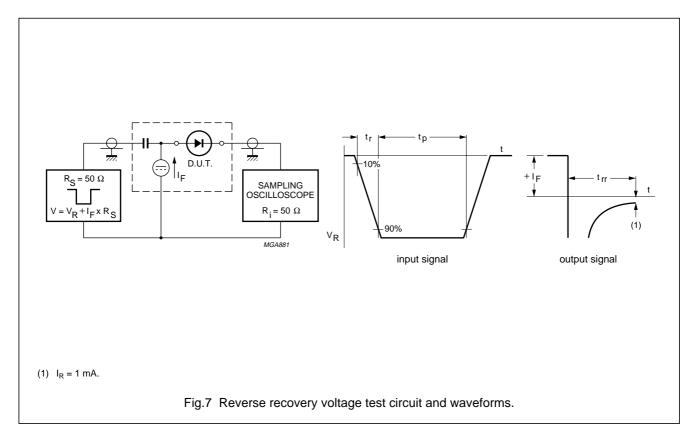
f = 1 MHz;  $T_j = 25$  °C.

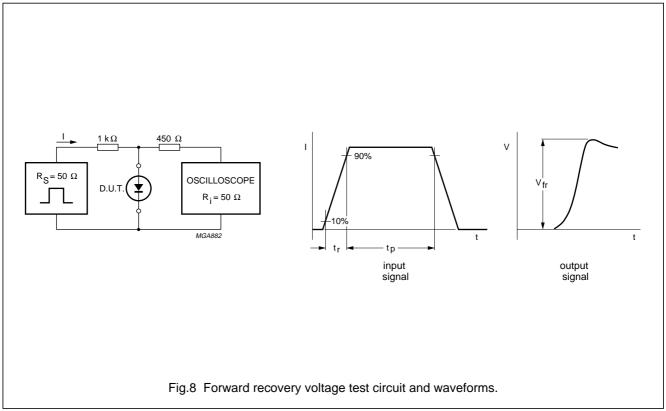
Diode capacitance as a function of reverse voltage; typical values.

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## High-speed diode

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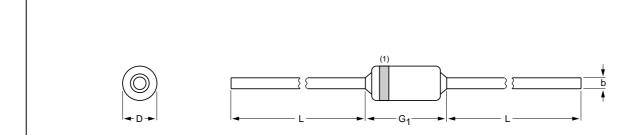
#### High-speed diode

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#### **PACKAGE OUTLINE**

#### Hermetically sealed glass package; axial leaded; 2 leads

SOD27



#### **DIMENSIONS** (mm are the original dimensions)

UNIT	b max.	D max.	G <sub>1</sub> max.	L min.	
mm	0.56	1.85	4.25	25.4	

0 1 2 mm

#### Note

1. The marking band indicates the cathode.

OUTLINE	REFERENCES EUROPEAN ISSUE			EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DATE	ISSUE DATE
SOD27	A24	DO-35	SC-40			97-06-09

#### **DEFINITIONS**

Data Sheet Status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			

#### **Limiting values**

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### Application information

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

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